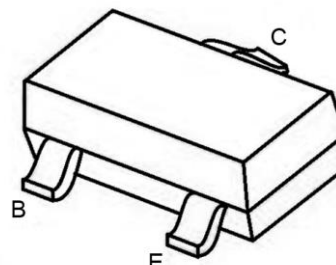


GPB8550S Transistor(PNP)

Features:

- PNP Epitaxial Silicon , Planar Design
- Collector-Emitter Voltage $V_{CE}=-25V$
- Collector Current $I_C=-1.5A$
- In Compliance with ER Rohs 2002/95/EC Directives
- Transition Frequency $f_T > 100MHz @ I_C=-50mA$,
 $V_{CE}=-10V, f=30MHz$

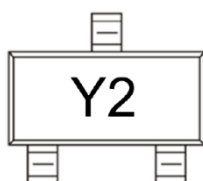
SOT-23



MAXIMUM RATINGS ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-1.5	A
Power Dissipation	P_d	0.3	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	417	$^{\circ}C/W$
Junction Temperature	T_J	-55~ +150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$

MARKING:



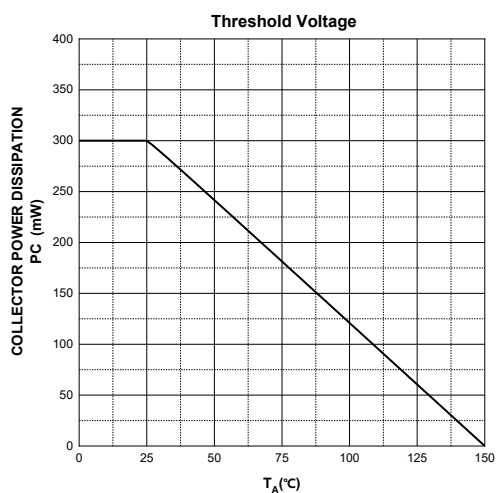
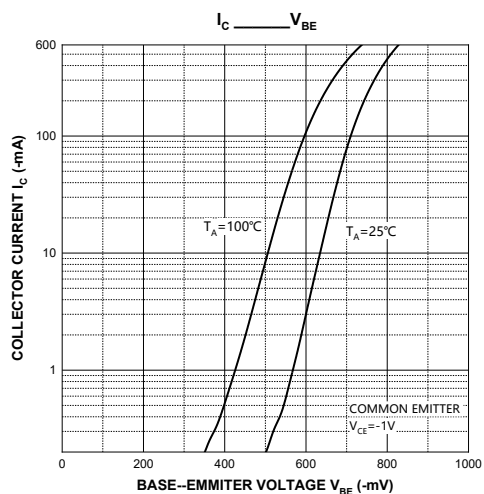
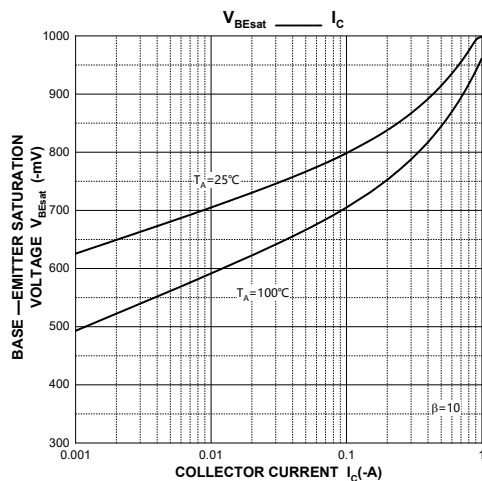
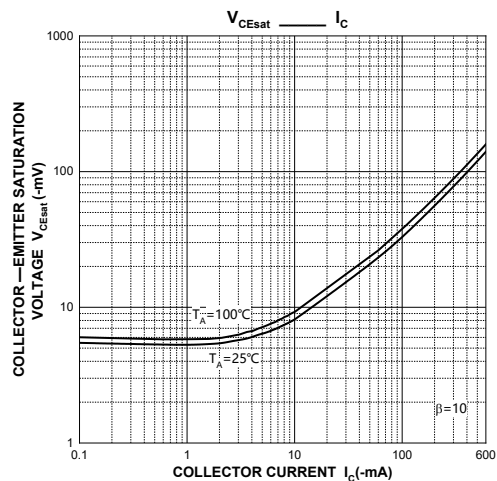
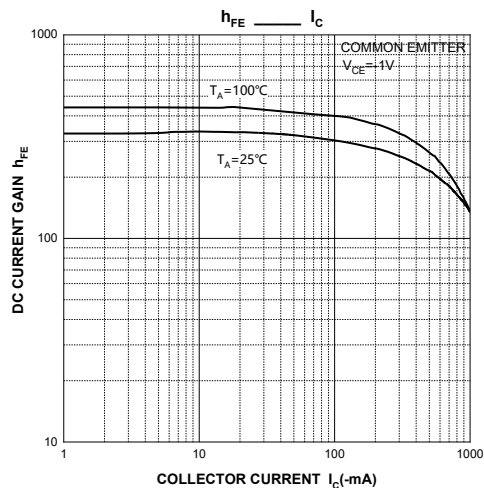
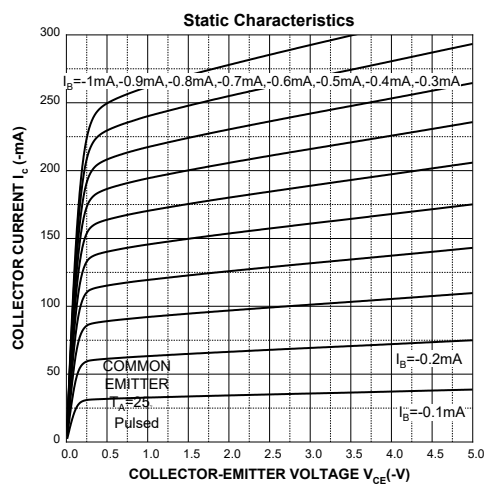
Classification of hfe:

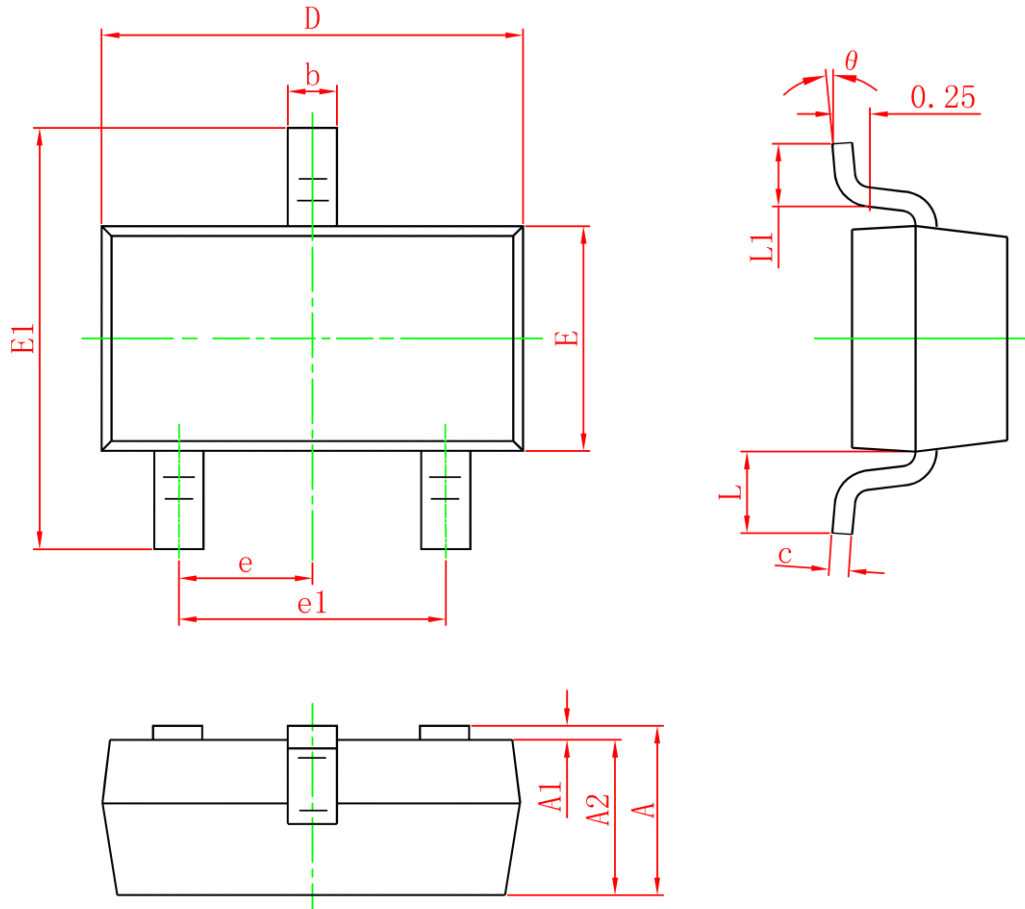
RANK	L	H	J
RANGE	120~200	200~350	350~400

ELECTRICAL CHARACTERISTICS($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-40		V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-25		V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5		V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -40\text{V}, I_E = 0$		-100	nA
Collector Cut-Off Current	I_{CEO}	$V_{CE} = -20\text{V}, I_B = 0$		-100	nA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$		-100	nA
DC Current Gain	h_{FE}	$V_{CE} = -1\text{V}, I_C = -0.1\text{mA}$	40		
	h_{FE}	$V_{CE} = -1\text{V}, I_C = -1\text{mA}$	70		
	h_{FE}	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$	120	400	
	h_{FE}	$V_{CE} = -1\text{V}, I_C = -400\text{mA}$	60		
	h_{FE}	$V_{CE} = -1\text{V}, I_C = -800\text{mA}$	30		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$		-0.5	V
		$I_C = -800\text{mA}, I_B = -80\text{mA}$		-0.6	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$		-1.1	V
		$I_C = -800\text{mA}, I_B = -80\text{mA}$		-1.2	V
Transition Frequency	f_T	$V_{CE} = -10\text{V}, I_C = -50\text{mA},$ $f = 30\text{MHz}$	100		MHZ
Collector Output Capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		20	pF

Typical Characteristics



SOT-23 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0	0.100	0	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.150	1.500	0.045	0.059
E1	2.250	2.650	0.089	0.104
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customers are solely responsible for providing adequate safe measures when design their systems.
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